Silicon Switching Diode

1N4153, 1N4153-1

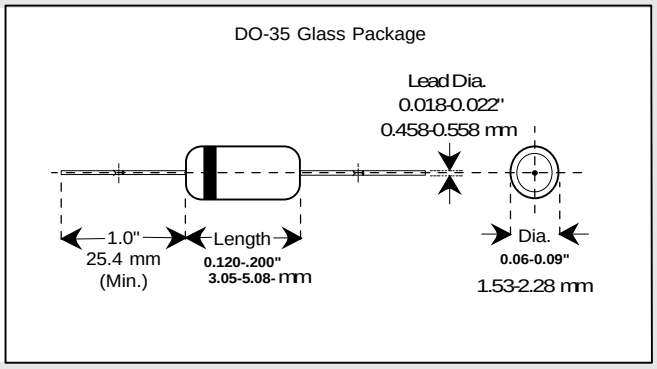
DO-35 Glass Package

Applications

Used in general purpose applications,where a low current controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/337
- Available up to JANTXV-1 levels
- "S" level screening available to SCDs



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	75 (Min.)	Volts
Average Rectified Current	I_{Avg}	150	mAmps
Continuous Forward Current	I_{Fdc}	300	mAmps
Peak Surge Current (t_{peak} = 1 Sec.)	I_{peak}	0.25	Amp
BKC Power Dissipation T_L = 50 °C, L = 3/8" from body	P_{tot}	500	mWatts
Operating and Storage Temperature Range	$T_{Op\ \&\ St}$	-65 to +200	°C

Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage @ I_F = 100 µA	V_F	Vf	0.49	0.55	Volts
Forward Voltage @ I_F = 250 µA	V_F	Vf	0.53	0.59	Volts
Forward Voltage @ I_F = 1.0 mA	V_F	Vf	0.59	0.67	Volts
Forward Voltage @ I_F = 2.0 mA	V_F	Vf	0.62	0.70	Volts
Forward Voltage @ I_F = 10 mA	V_F		0.70	0.81	Volts
Forward Voltage @ I_F = 20 mA	V_F		0.74	0.88	Volts
Reverse Leakage Current @ V_R = 50 V	I_R			0.05(50 @ 150 °C)	µA
Breakdown Voltage @ I_R = 5.0 µA	PIV		75		Volts
Capacitance @ V_R = 0 V, f = 1mHz	C_T			2.0	pF
Reverse Recovery Time (note 1)	t_{rr}			4.0	nSecs
Reverse Recovery Time (note 2)	t_{rr}			2.0	nSec

Note 1: Per Method 4031-A with I_F = I_R = 10 mA, R_L = 100 Ohms, C = 3 Pf. *Unless Otherwise Specified

Note2: Per Method 4031-A with I_F = I_R = 10 mA, Rr = 6 Volts, Rl=100 ohms.

Microsemi

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